

Amendments to the Specification

IN THE TITLE

Please amend the title as follows:

--- SiC-FORMED MATERIAL ~~AND METHOD FOR MANUFACTURING SAME~~ ---

IN THE SPECIFICATION - SUMMARY OF THE INVENTION

Please replace the paragraph beginning at page 4, line 19, with the following rewritten paragraph:

a<sup>1</sup> ---To achieve the above object, the SiC-formed material of ~~claim 1~~ of the present invention is an SiC-formed material produced by the CVD method using nitrogen gas together with raw material gases, characterized by possessing a specific gravity of 3.15 or more, light transmittance of 1.1 to 0.05%, and resistivity of  $3 \times 10^{-3}$  to  $10^{-5}$   $\Omega\text{m}$ .---

Please replace the paragraph beginning at page 4, line 25, with the following rewritten paragraph:

a<sup>2</sup> ---The method for manufacturing the SiC-formed material of ~~claim 2~~ of the present invention comprises producing an SiC film on the surface of a substrate by the CVD method using nitrogen gas together with raw material gases, and removing the substrate to obtain the SiC-formed material, wherein the raw material gas concentration, in terms of the ratio of the raw material flow rate (l/min) to the carrier gas flow rate (l/min) introduced into the CVD reaction chamber in which the substrate is located, is 5-15 vol%, the nitrogen gas concentration, in terms of the ratio of the nitrogen gas flow rate (l/min) to the raw material gas flow rate (l/min), is 10-120 vol%, the raw material gas resident time defined by the following formula is controlled to 7-110 seconds, and the deposition rate is controlled to 20-400  $\mu\text{m}/\text{hour}$ .